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Synthesis and Characterization of Silicon Nanowires: Towards Devices and Applications

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Synthesis and characterization of silicon 07. nanowires: towards devices and applications

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Outline

Si Nanowires: Fabrication and characterization

- CVD growth / doping
- wet chemical etching
- > Applications:
- Matrix-free Desorption / Ionization Mass Spectrometry
- Surface Enhanced Raman Scattering (SERS)
- Solar cells
- Chemical and biological sensors



Synthesis and characterization of silicon 07. nanowires: towards devices and applications

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Synthesis and characterization of silicon 07.12.2 nanowires: towards devices and applications

Vapour-liquid-solid (VLS) growth process



R.S. Wagner and W.C. Ellis, Appl. Phys. Lett. 4 (1964) 89





Metal templates

Immobilized Au nanoparticles





Au dots by EBL





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Chemical vapour deposition (CVD)





Gases: Ar, He, H₂, SiH₄, B₂H₆, PH₃ Temperature: $\leq 600^{\circ}$ C



Synthesis and characterization of silicon (nanowires: towards devices and applications

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CVD VLS growth

random or epitaxial growth





diameter controlled growth







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Structural quality

TEM









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Electrical properties / doping

Electron beam induced current (EBIC) imaging



20 sccm Ar / 4 sccm SiH₄ 0.1 sccm B_2H_6 (100 ppm in He)

 $0.1-0.6 \ \Omega cm \ / \ 1-8 \ x \ 10^{16} cm^{-3}$



20 sccm Ar / 4 sccm SiH₄ 0.1 sccm PH_3 (100 ppm in He)

 $0.1-0.2 \ \Omega cm \ / \ 8x10^{16}-2x10^{17} \ cm^{-3}$







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Resistivity of individually contacted Si-NRs

Si-NRs contacted by metal electrodes in a multi-terminal layout using e-beam lithography





Synthesis and characterization of silicon 07.12.20 nanowires: towards devices and applications



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Wet chemical etching of Si



K. Peng, A. Lu, R. Zhang, S.-T. Lee, Adv. Funct. Mater. 18 (2008) 3026

first step: $AgNO_3 / HF$ followed by: H_2O_2 / HF





Synthesis and characterization of silicon 07.12 nanowires: towards devices and applications

Structural quality / Photoluminescence









Synthesis and characterization of silicon 07.12.20 nanowires: towards devices and applications



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Synthesis and characterization of silicon 07.12.20 nanowires: towards devices and applications

Matrix-free Laser Desorption / Ionization Mass Spectrometry

A. Muck, A. Svatoš (MPI for Chemical Ecology Jena)



matrix-assisted laser desorption/ ionization (MALDI): + soft ionization, high sensitivity - matrix background signals

laser desorption / ionization from SiNWs:

+ much lower laser energy to desorb molecules,

absorption maximum of SiNWs near the wavelength of the laser (337 nm), heating of the silicon core within the insulating oxide sheath

+ high surface area, wick fluids



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Preparation of MALDI chips

standard MALDI chip (5,5 x 4,1 cm) chip IPHT Jena (2,54 x 2,54 cm)





2. tailored SiNW surface chemistry

A. Muck, T. Stelzner, U. Hübner, S. Christiansen, A. Svatoš, Lithographically Patterned Silicon Nanowire Arrays for matrix free LDI-TOF/MS Analysis of Lipids, Lab on a chip (2009) accepted



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SiNW based SERS substrates

Autometallography:

 catalytic reduction of silver ions to metallic silver on the surfaces of gold particles in the presence of reducing molecules

Gold caps atop SiNWs





TEM



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SERS spectra



crystal violet, ~1.7 x 10³ W/cm²







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Mapping of SERS intensity



crystal violet, HeNe laser (633 nm), ~160 µW, 3.5 µm spot size



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Solar cells - concepts

Thin film solar cells

- cheap substrates (glass, metal foils)
- Si nanorods with core-shell structure,
 - decouple absorption from charge transport by lateral diffusion of minority carriers

Axial and radial p-n junction





Wet chemical etching



max. efficiency: 4.4%



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Optical properties

Reflection and transmission measured with an integrating sphere (A=1-R-T)



diameter, (length, pitch)





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I-V characteristics

axial p-n junction

measurement setup







20 sccm Ar / 4 sccm SiH₄ 0.05 sccm B_2H_6 (2 % in He)

0.1-0.6 Ωcm / 1-8 x $10^{16}\ cm^{-3}$

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Core-shell p-n junction structures

a-Si with PECVD



h 20nm

600° C, 6



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Current work

EU project ROD_SOL

- elaborate cell concepts based on simulations
- avoid the use of Au as a catalyst
- single-crystalline core-shell p-n junction structures
- passivation and contacting of SiNWs



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SiNW field-effect transistors as sensors



- SiNWs: high surface to volume ratio, high carrier mobility, controlled functionalization
- sensors: ,lock-and-key' design

cross-reactive sensors in conjunction with pattern recognition



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Chemical modification of SiNW surfaces

M.Y. Bashouti, O. Assad, S.R. Puniredd, H. Haick (Technion-Israel Institute of Technology)



Functionalization





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Stability against oxidation



- all groups give nearly full coverage
- propenyl functionality:
 - combination of stability and subsequent covalent functionalization,



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Current work

- understanding of the signal transduction mechanism for various volatile organic compounds
- improved sensitivity in the presence of e.g. humidity
- develop sensor arrays to detect lung cancer



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Thank you for your attention!